Description

This 20V 11A is P-channel enhancement mode field effect transistor in a DFN 2 ×2B-6L plastic package.

Applications

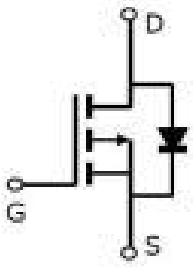
- Power management in notebook computer,
- Portable equipment and battery powered systems.

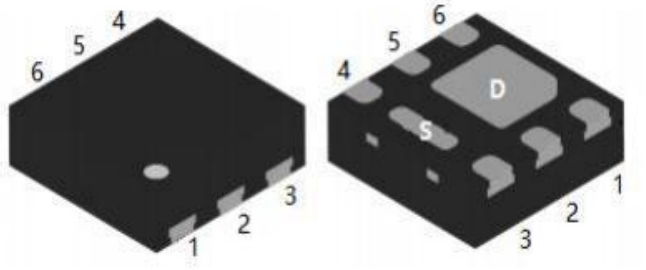
Features

- VDS (V) = -20V
- ID = -11A
- RDS(ON)@-4.5V≤17mΩ(Type.15mΩ)
- Halogen-Free Product

V_{DSS}	$R_{DS(on)}$Typ	I_D
20V	15mΩ	11A

Equivalent Circuit & Pinning





Pin1	D
Pin2	D
Pin3	G
Pin4	S
Pin5	D
Pin6	D

Marking

See Marking Instructions

Absolute Maximum Ratings(Ta=25℃)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±12	V
Continuous Drain Current		I_D (T_a=25°C)	-11	A
Pulsed Drain Current		I_{DM}	-44	A
Avalanche Current		I_{AS}	13	A
Avalanche energy L=0.5mH		E_{AS}	59	mJ
Power Dissipation for Single Operation		P_D (T_a=25℃)	3.0	W
Maximum Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 ~ 150	℃
Thermal Resistance-Junction to Ambient	t≦10s	$R_{\theta JA}$	40	℃/W
	Steady State		75	℃/W

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250μA V_{GS}=0V	-20	-23		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V V_{GS}=0V			-1.0	μA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V V_{GS}=±12V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS I_D=-250μA	-0.4	-0.7	-1.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V I_D=-10A		15	17	mΩ
		V_{GS}=-2.5V I_D=-5A		19	25	
		V_{GS}=-1.8V I_D=-1A		27	38	
Diode Forward Voltage	V_{SD}	I_S=-1A V_{GS}=0V			-1.2	V
Total Gate Charge	Q_g	V_{GS}=-4.5V V_{DS}=-6V I_D=-8A		12.7		nC
Gate-Source Charge	Q_{gs}			1.7		
Gate-Drain Charge	Q_{gd}			3.4		
Gate resistance	Rg	V_{GS}=0V, V_{DS}=0V, f=1MHz		13.5		
Input Capacitance	C_{iss}	V_{GS}=0V V_{DS}=-20V f=1MHz		2550		pF
Output Capacitance	C_{oss}			205		
Reverse Transfer Capacitance	C_{rss}			190		
Turn-on Delay Time	$t_{d(ON)}$	V_{GS}=-4.5V V_{DS}=-6V R_{GEN}=3Ω R_L=0.75Ω		11		ns
Turn-on Rise Time	t_r			25		
Turn-off Delay Time	$t_{d(OFF)}$			70		
Turn-off Fall Time	t_f			41.5		

Electrical Characteristic Curve

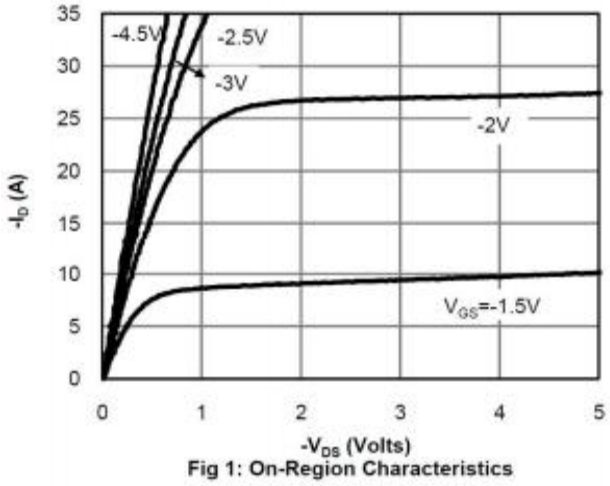


Fig 1: On-Region Characteristics

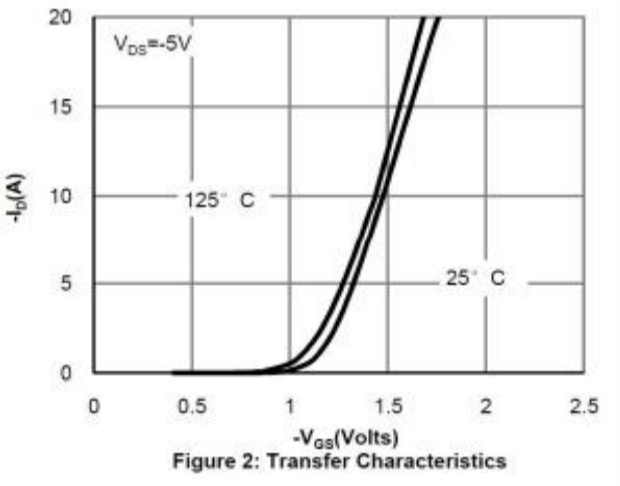


Figure 2: Transfer Characteristics

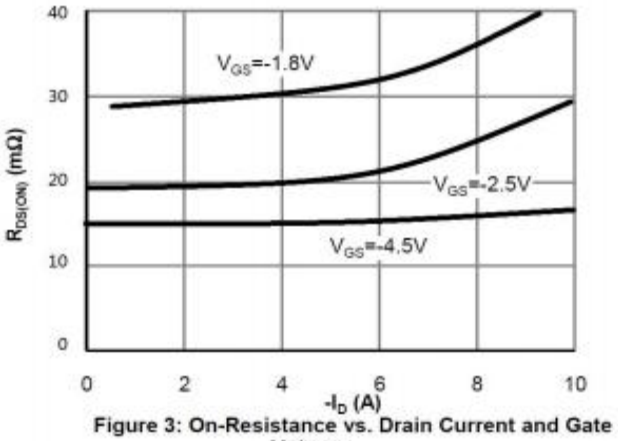


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

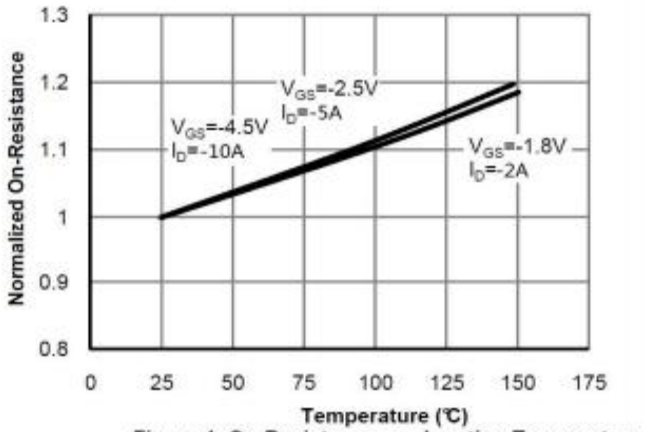


Figure 4: On-Resistance vs. Junction Temperature

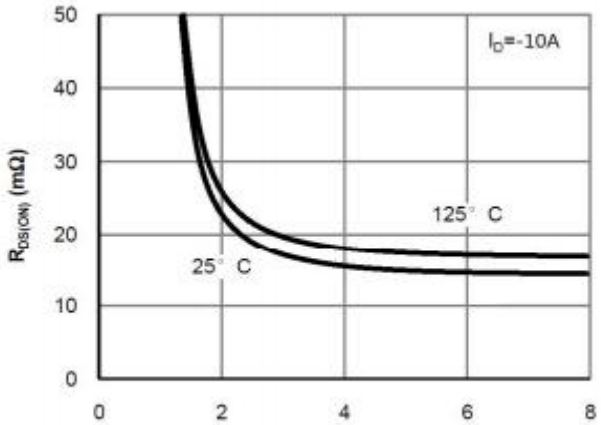


Figure 5: On-Resistance vs. Gate-Source Voltage

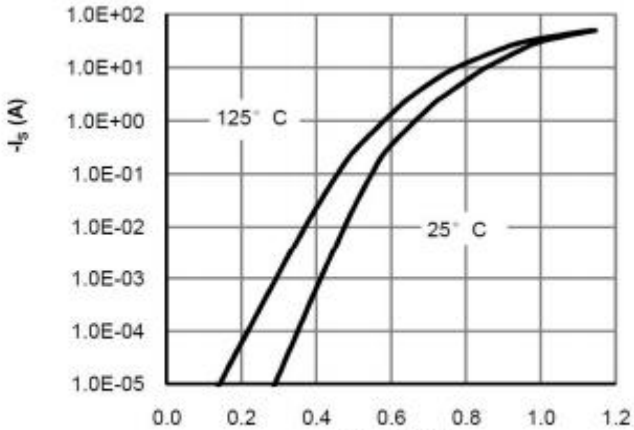


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

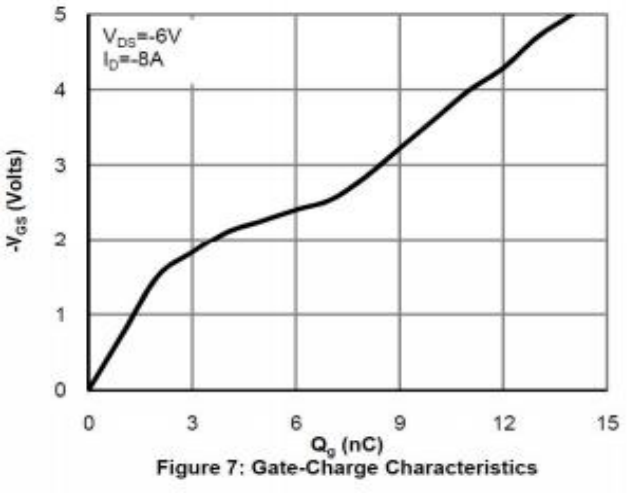


Figure 7: Gate-Charge Characteristics

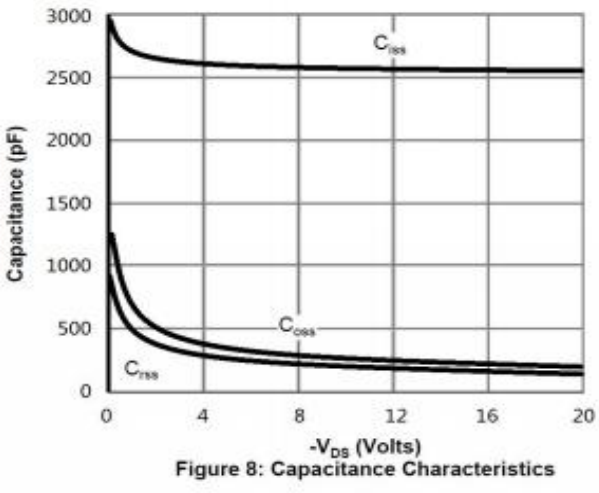
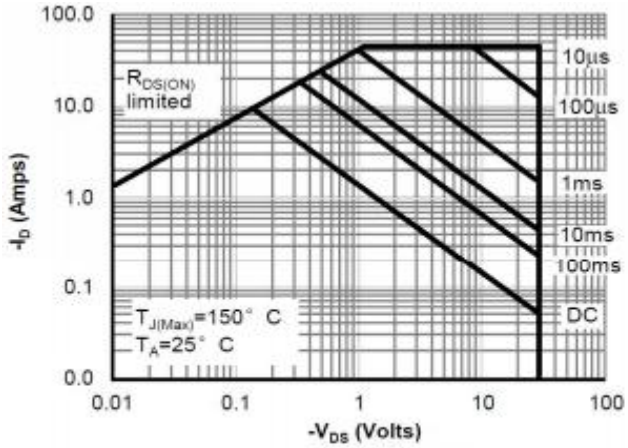


Figure 8: Capacitance Characteristics



V_{GS}> or equal to -4.5V

Figure 9: Maximum Forward Biased Safe Operating Area

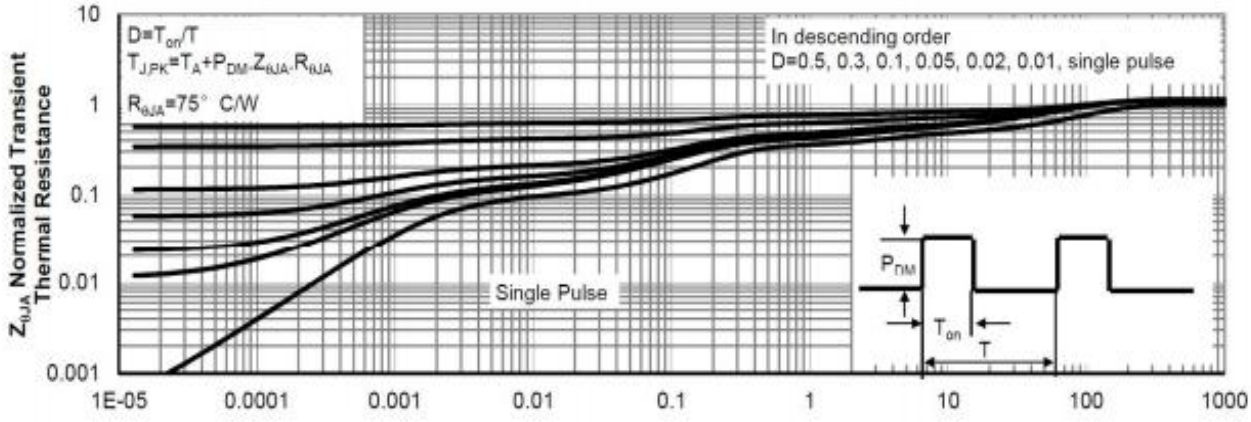
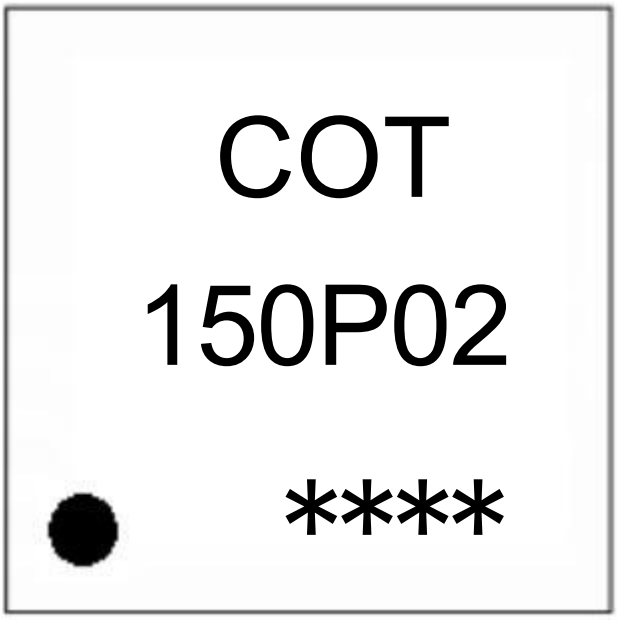


Figure 10: Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

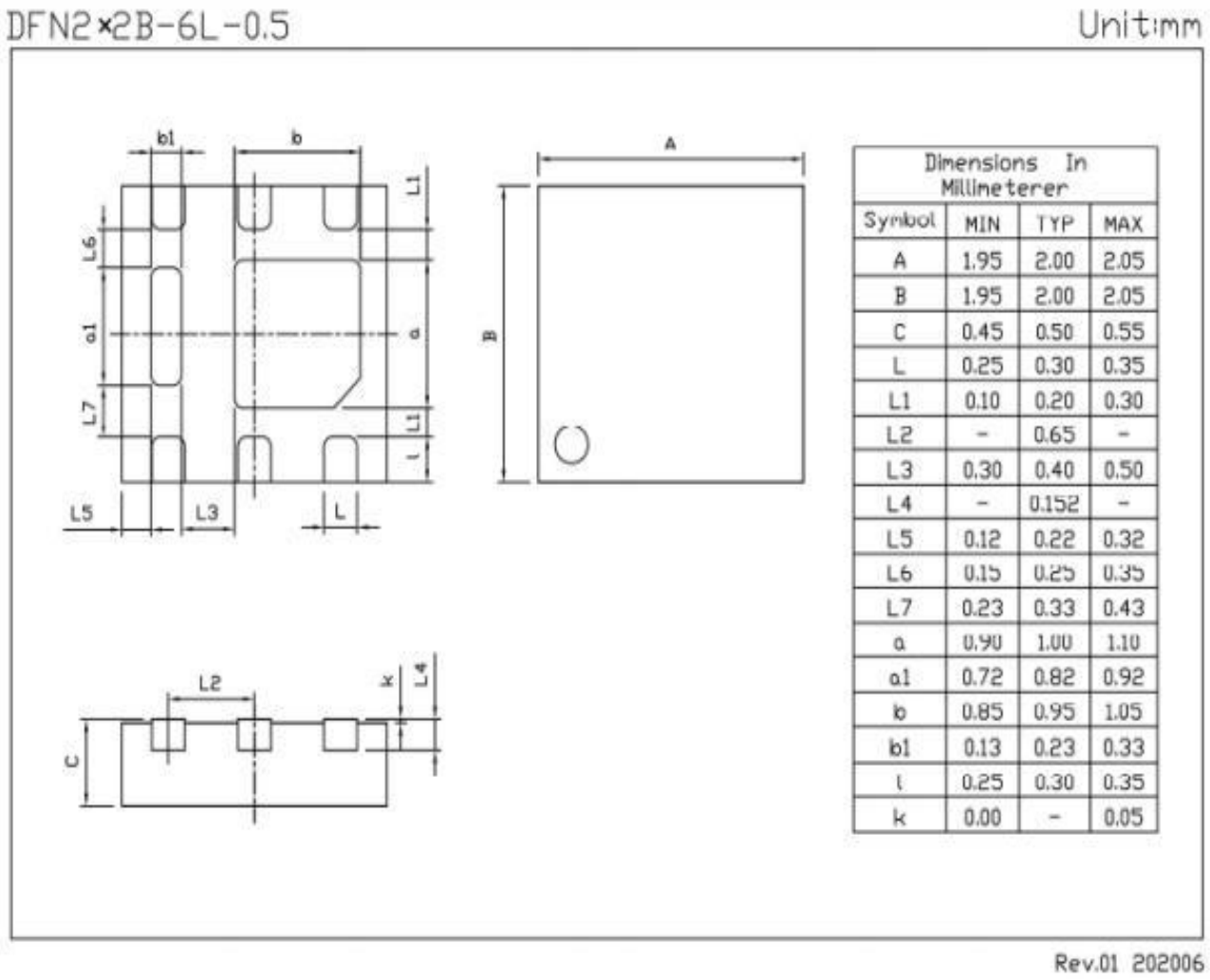
COT:	Company Code
150P02:	Product Type
****:	Lot No. Code, code change with Lot No

Packaging SPEC.

REEL INFORMATION

Package Type	Units					Dimension (unit：mm³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
DFN 2×2B-6L	4,000	10	40,000	4	160,000	7″ ×8	210×205×205	445×230×435

Package Outline Dimensions



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	1.95	2.00	2.05
B	1.95	2.00	2.05
C	0.45	0.50	0.55
L	0.25	0.30	0.35
L1	0.10	0.20	0.30
L2	-	0.65	-
L3	0.30	0.40	0.50
L4	-	0.152	-
L5	0.12	0.22	0.32
L6	0.15	0.25	0.35
L7	0.23	0.33	0.43
a	0.90	1.00	1.10
a1	0.72	0.82	0.92
b	0.85	0.95	1.05
b1	0.13	0.23	0.33
l	0.25	0.30	0.35
k	0.00	-	0.05

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